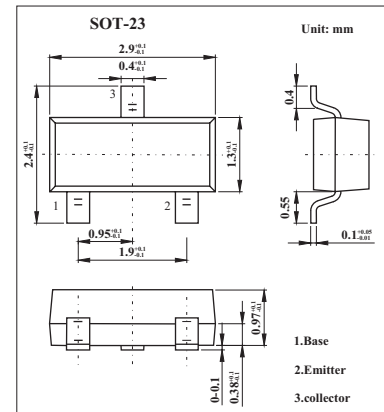


NPN General Purpose Transistors

BCX20

■ Features

- General Purpose Transistors.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-emitter voltage	V_{CES}	30	V
Collector-emitter voltage	V_{CEO}	25	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	800	A
Collector dissipation	P_C	310	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-65 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Max	Unit
Collector-emitter breakdown voltage	BV_{CEO}	$I_C = 10\text{mA}, I_B = 0$	25		V
Collector-emitter breakdown voltage	BV_{CES}	$I_C = 100\mu\text{A}, V_{BE} = 0$	30		V
Emitter-base breakdown voltage	BV_{EBO}	$I_E = 10\mu\text{A}, I_C = 0$	5		V
Collector cut-off current	I_{CBO}	$V_{CE} = 20\text{V}, V_{BE} = 0$		100	nA
Emitter-base cut-off current	I_{EBO}	$V_{BE} = 5\text{V}, I_C = 0$		10	nA
DC current gain	h_{FE}	$V_{CE} = 1\text{V}, I_C = 100\text{mA}$	100	600	
		$V_{CE} = 1\text{V}, I_C = 300\text{mA}$	70		
		$V_{CE} = 1\text{V}, I_C = 500\text{mA}$	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$		0.62	V
Base-emitter saturation voltage	$V_{BE(on)}$	$V_{CE} = 1\text{A}, I_B = 500\text{mA}$		1.2	V

■ Marking

Marking	U2